



CHENYI ELECTRONICS

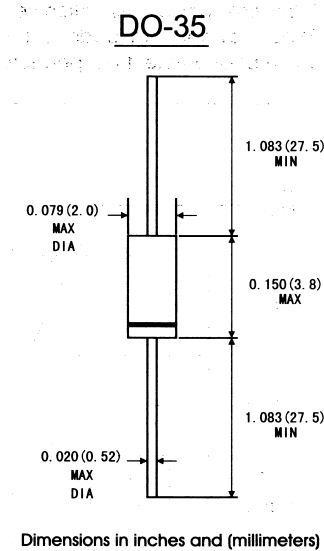
BZX55-C0V8 THRU BZX55-C200
0.5W SILICON PLANAR ZENER DIODES

FEATURES

- . The zener voltage are graded according to the international E24 standard .Other voltage tolerance and higher zener voltage on request.

MECHANICAL DATA

- . **Case:** DO-35 glass case
- . **Polarity:** Color band denotes cathode end
- . **Weight:** Approx. 0.13gram



ABSOLUTE MAXIMUM RATINGS(LIMITING VALUES)(TA=25℃)

	Symbols	Value	Units
Zener current see table "Characteristics"			
Power dissipation at TA=50℃	Ptot	5001)	mW
Junction temperature	TJ	175	℃
Storage temperature range	TSTG	-65 to + 175	℃
1)Valid provided that at a distance of 8mm from case are kept at ambient temperature			

ELECTRICAL CHARACTERISTICS(TA=25℃)

	Symbols	Min.	Typ.	Max.	Units
Thermal resistance junction to ambient	R θJA			3001)	K/W
Forward voltage at IF=100mA	VF			1	V
1)Valid provided that leads at a distance of 8mm from case are kept at ambient temperature					

BZX55... SILICON PLANAR ZENER DIODES

Type	Zener Voltage Range1)			Dynamic resistance			Reverse leakage current			Temp coefficient of zener voltage
	VZNOM	IZT for VZT 2)		r _{zjt} and r _{zjk} at I _{zk}			I _R and I _{R 2)} at V _R			TK _{vz}
	V	mA	V	Ω	Ω	mA	μ A	μ A	V	%/K
BZX 55/C 0V8 3)	0.8	5	0.73.0.83	<8	<50	1	-	-	-	-0.26...-0.23
BZX 55/C 2V0	2.0		1.9.2.1	<85	<600		<100	<200	<1	-0.09...-0.06
BZX 55/C 2V4	2.4		2.28.2.56				<50	<100		
BZX 55/C 2V7	2.7		2.5.2.9				<10	<50		
BZX 55/C 3V0	3		2.8.3.2				<4	<40		-0.08...-0.05
BZX 55/C 3V3	3.3		3.1.3.5							
BZX 55/C 3V6	3.6		3.4.3.8							
BZX 55/C 3V9	3.9		3.7.4.1				<75	<1		<20
BZX 55/C 4V3	4.3		4.0.4.6	<0.5				<10		-0.05...+0.02
BZX 55/C 4V7	4.7		4.4.5.0	<60			<0.1	<2		-0.02...+0.02
BZX 55/C 5V1	5.1		4.8.5.4	<35	<550				-0.05...+0.05	
BZX 55/C 5V6	5.6		5.2.6.0	<25	<450				2.0	0.03.0.06
BZX 55/C 6V2	6.2		5.8.6.6	<10	<200				3.0	0.03.0.07
BZX 55/C 6V8	6.8		6.4.7.2	<8	<150				5.0	0.03.0.07
BZX 55/C 7V5	7.5		7.0.7.9	<7	<50				6.2	0.03.0.08
BZX 55/C 8V2	8.2		7.7.8.7	<7					6.8	0.03.0.09
BZX 55/C 9V1	9.1		8.5.9.6	<10					7.5	0.03.0.1
BZX 55/C 10	10		9.4.10.6	<15	<70				8.2	0.03.0.11
BZX 55/C 11	11		10.4.11.6	<20	<70				9.1	
BZX 55/C 12	12		11.4.12.7	<20	<90				10.0	
BZX 55/C 13	13		12.4.14.1	<26	<110				11.0	
BZX 55/C 15	15		13.8.15.6	<30	<110				12	
BZX 55/C 16	16		15.3.17.1	<40	<170				13	
BZX 55/C 18	18		16.8.19.1	<50	<170				15	
BZX 55/C 20	20		18.8.21.2	<55	<220					

BXZ55... SILICON PLANAR ZENER DIODES

BZX 55/C 22	22	5	20.8.23.3	<55	<220	1	<0.1	<2	16	0.04.0.12	
BZX 55/C 24	24		22.8.25.6	<80					18		
BZX 55/C 27	27		25.1.28.9	<80					20		
BZX 55/C 30	30		28.32						22		
BZX 55/C 33	33		31.35						24		
BZX 55/C 36	36		34.38						27		
BZX 55/C 39	39	2.5	37.41		<500	0.5		<5	30		0.05.0.12
BZX 55/C 43	43		40.46		<500				33		
BZX 55/C 47	47		44.50		<600				36		
BZX 55/C 51	51		48..54		<700			39			
BZX 55/C 56	56		52.60		<700			43			
BZX 55/C 62	62		58.66		<1000			47			
BZX 55/C 68	68		64..72					51			
BZX 55/C 75	75		70..79					56			
BZX 55/C 82	82		77.87		<1500	0.25			62		
BZX 55/C 91	91	1	85.96		<2000	0.1		<10	68		
BZX 55/C 100	100		94.106		<5000				75		
BZX 55/C 110	110		104.116		<5000				82		
BZX 55/C 120	120		114.127		<5500				91		
BZX 55/C 130	130		124.141		<6000				100		
BZX 55/C 150	150		138.156		<6500				110		
BZX 55/C 160	160		153.171		<7000				120		
BZX 55/C 180	180		168.191		<8500				130		
BZX 55/C 200	200			188.212					<10000		

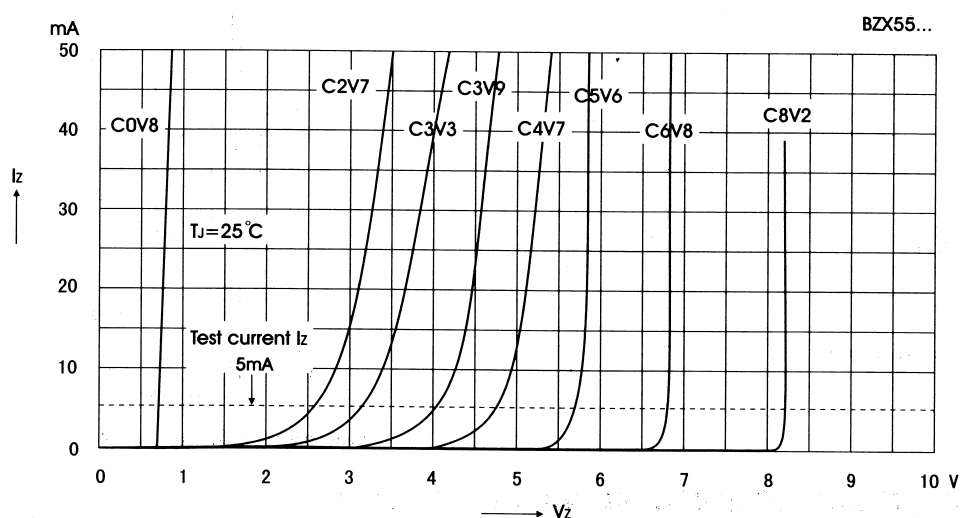
1) Tested with pulses $t_p=20\text{ms}$

2) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case

3) The BZX55-C0V8 is silicon diode with operation in forward direction. Hence, the index of all parameters should be 'F' instead of 'Z'. Connect the cathode lead to the negative pole.

BZX55... SILICON PLANAR ZENER DIODES

BREAKDOWN CHARACTERISTICS AT $T_J = \text{CONSTANT}$ (PULSED)



BREAKDOWN CHARACTERISTICS AT $T_J = \text{CONSTANT}$ (PULSED)

